

PNP - 2N6107, 2N6109, 2N6111; NPN - 2N6288, 2N6292

2N6109 and 2N6292 are Preferred Devices

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- DC Current Gain Specified to 7.0 Amperes
 $h_{FE} = 30-150 @ I_C$
 $= 3.0 \text{ Adc} - 2N6111, 2N6288$
 $= 2.3 (\text{Min}) @ I_C = 7.0 \text{ Adc} - \text{All Devices}$
- Collector-Emitter Sustaining Voltage -
 $V_{CEO(sus)} = 30 \text{ Vdc} (\text{Min}) - 2N6111, 2N6288$
 $= 50 \text{ Vdc} (\text{Min}) - 2N6109$
 $= 70 \text{ Vdc} (\text{Min}) - 2N6107, 2N6292$
- High Current Gain - Bandwidth Product
 $f_T = 4.0 \text{ MHz} (\text{Min}) @ I_C = 500 \text{ mAdc} - 2N6288, 90, 92$
 $= 10 \text{ MHz} (\text{Min}) @ I_C = 500 \text{ mAdc} - 2N6107, 09, 11$
- TO-220AB Compact Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V_{CEO}	30 50 70	Vdc
Collector-Base Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V_{CB}	40 60 80	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current - Continuous - Peak	I_C	7.0 10	Adc
Base Current	I_B	3.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

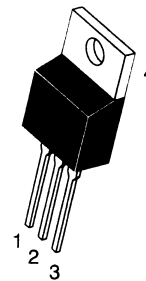
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

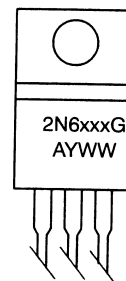
1. Indicates JEDEC Registered Data.

7 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 30 - 50 - 70 VOLTS, 40 WATTS

MARKING DIAGRAM



TO-220AB
 CASE 221A
 STYLE 1



2N6xxx = Specific Device Code
 xxx = See Table on Page 4
 G = Pb-Free Package
 A = Assembly Location
 Y = Year
 WW = Work Week

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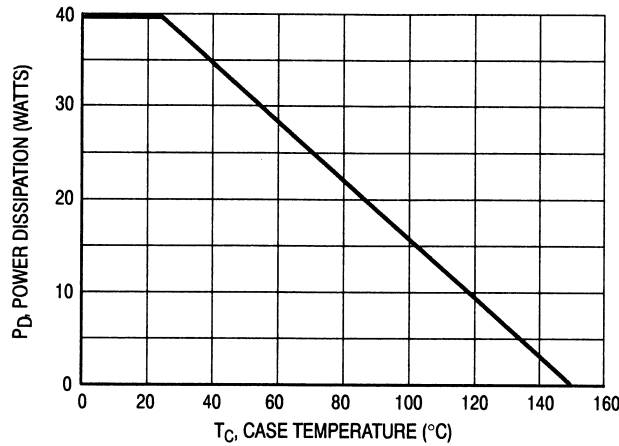


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

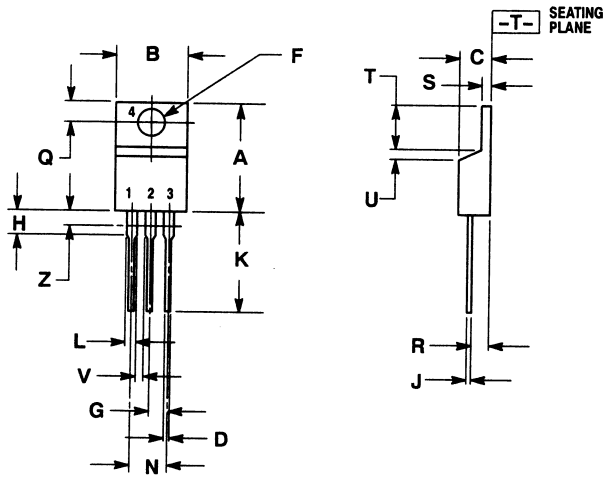
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 100\text{ mA}$, $I_B = 0$)	$V_{CE(sus)}$			Vdc
2N6111, 2N6288		30	-	
2N6109		50	-	
2N6107, 2N6292		70	-	
Collector Cutoff Current ($V_{CE} = 20\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CEO}	-	1.0	mAdc
2N6111, 2N6288		-	1.0	
2N6109		-	1.0	
2N6107, 2N6292		-	1.0	
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 80\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 30\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 50\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 70\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	-	100	μAdc
2N6111, 2N6288		-	100	
2N6109		-	100	
2N6107, 2N6292		-	100	
2N6111, 2N6288		-	2.0	mAdc
2N6109		-	2.0	
2N6107, 2N6292		-	2.0	
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	1.0	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain ($I_C = 2.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 2.5\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 7.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	30	150	-
2N6107, 2N6292		30	150	
2N6109		30	150	
2N6111, 2N6288		30	150	
All Devices		2.3	-	
Collector-Emitter Saturation Voltage ($I_C = 7.0\text{ Adc}$, $I_B = 3.0\text{ Adc}$)	$V_{CE(sat)}$	-	3.5	Vdc
Base-Emitter On Voltage ($I_C = 7.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	-	3.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product (Note 4) ($I_C = 500\text{ mA}$, $V_{CE} = 4.0\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	4.0	-	MHz
2N6288, 92		10	-	
2N6107, 09, 11				
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	-	250	pF
Small-Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 50\text{ kHz}$)	h_{fe}	20	-	-

2. Indicates JEDEC Registered Data.
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
4. $f_T = |h_{fe}| \cdot f_{test}$

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PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AE



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04